**Product data sheet** 

# 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006-3 (SOT883) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- Leadless ultra small SMD plastic package: 1.0 × 0.6 × 0.48 mm

## 3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

| Symbol            | Parameter                        | Conditions  |     | Min | Тур | Max | Unit |
|-------------------|----------------------------------|---|-----|-----|-----|-----|------|
| $V_{DS}$          | drain-source voltage             | T <sub>j</sub> = 25 °C                            |     | -   | -   | 20  | V    |
| $V_{GS}$          | gate-source voltage              |   |     | -8  | -   | 8   | V    |
| I <sub>D</sub>    | drain current                    | V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C | [1] | -   | -   | 1   | Α    |
| Static characte   | Static characteristics           |   |     |     |     |     |      |
| R <sub>DSon</sub> | drain-source on-state resistance | $V_{GS}$ = 4.5 V; $I_D$ = 500 mA; $T_j$ = 25 °C   |     | -   | 290 | 380 | mΩ   |

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



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# 5. Pinning information

### Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline                       | Graphic symbol |
|-----|--------|-------------|--|----------------|
| 1   | G      | gate        | 1  | D<br>I         |
| 2   | S      | source      | 2 🔲 📗 3                                  |                |
| 3   | D      | drain       | Transparent top view  DFN1006-3 (SOT883) | G S 017aaa255  |

# 6. Ordering information

#### Table 3. Ordering information

| Type number | Package   |   |         |  |  |  |
|-------------|-----------|---|---------|--|--|--|
|             | Name      | Description   | Version |  |  |  |
| PMZ290UNE   | DFN1006-3 | DFN1006-3: leadless ultra small plastic package; 3 solder lands | SOT883  |  |  |  |

# 7. Marking

#### Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PMZ290UNE   | ZS           |

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# **Limiting values**

Table 5. **Limiting values** 

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter                       | Conditions   |     | Min | Max  | Unit |
|------------------|---------------------------------|--|-----|-----|------|------|
| V <sub>DS</sub>  | drain-source voltage            | T <sub>j</sub> = 25 °C                             |     | -   | 20   | V    |
| V <sub>GS</sub>  | gate-source voltage             |  |     | -8  | 8    | V    |
| I <sub>D</sub>   | drain current                   | V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C  | [1] | -   | 1    | Α    |
|                  |                                 | V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C | [1] | -   | 625  | mA   |
| I <sub>DM</sub>  | peak drain current              | $T_{amb}$ = 25 °C; single pulse; $t_p \le 10$ μs   |     | -   | 4    | Α    |
| P <sub>tot</sub> | total power dissipation         | T <sub>amb</sub> = 25 °C                           | [2] | -   | 360  | mW   |
|                  |                                 |  | [1] | -   | 715  | mW   |
|                  |                                 | T <sub>sp</sub> = 25 °C                            |     | -   | 2700 | mW   |
| Tj               | junction temperature            |  |     | -55 | 150  | °C   |
| T <sub>amb</sub> | ambient temperature             |  |     | -55 | 150  | °C   |
| T <sub>stg</sub> | storage temperature             |  |     | -65 | 150  | °C   |
| Source-dra       | ain diode                       |  | '   |     |      |      |
| Is               | source current                  | T <sub>amb</sub> = 25 °C                           | [1] | -   | 680  | mA   |
| ESD maxin        | num rating                      |  |     | -1  |      | 1    |
| V <sub>ESD</sub> | electrostatic discharge voltage | НВМ  | [3] | -   | 2000 | V    |

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>. Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard

Measured between all pins. [3]

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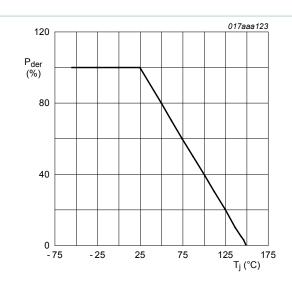


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

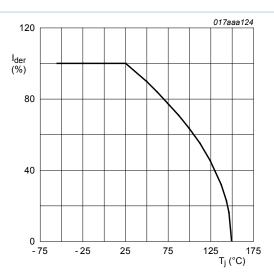
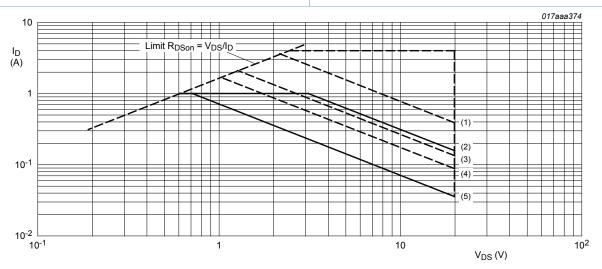


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$



I<sub>DM</sub> = single pulse

 $(1) t_p = 1 ms$ 

(2) DC;  $T_{sp}$  = 25 °C

(3)  $t_0 = 10 \text{ ms}$ 

(4)  $t_p = 100 \text{ ms}$ 

(5) DC;  $T_{amb}$  = 25 °C; drain mounting pad 1 cm<sup>2</sup>

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

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## **Thermal characteristics**

Table 6. **Thermal characteristics** 

PMZ290UNE

| Symbol                | Parameter  | Conditions |     | Min | Тур | Max | Unit |
|-----------------------|--|------------|-----|-----|-----|-----|------|
| R <sub>th(j-a)</sub>  | thermal resistance from junction to ambient      | _          | [1] | -   | 305 | 360 | K/W  |
|                       |  |            | [2] | -   | 150 | 175 | K/W  |
| R <sub>th(j-sp)</sub> | thermal resistance from junction to solder point |            |     | -   | -   | 40  | K/W  |

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

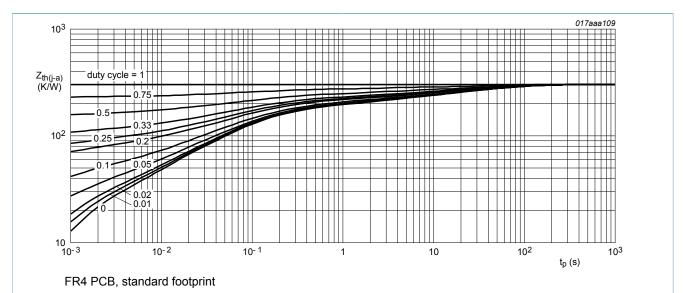


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

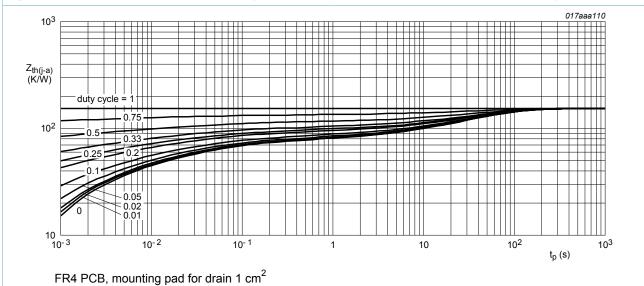


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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## 10. Characteristics

#### Table 7. Characteristics

| Symbol              | Parameter                         | Conditions   | Min  | Тур  | Max  | Unit |
|---------------------|-----------------------------------|--|------|------|------|------|
| Static chara        | acteristics                       |  | '    |      |      |      |
| $V_{(BR)DSS}$       | drain-source<br>breakdown voltage | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$                               | 20   | -    | -    | V    |
| $V_{GSth}$          | gate-source threshold voltage     | $I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$                    | 0.5  | 0.75 | 0.95 | V    |
| I <sub>DSS</sub>    | drain leakage current             | V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C      | -    | -    | 1    | μΑ   |
|                     |                                   | V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C     | -    | -    | 10   | μΑ   |
| I <sub>GSS</sub>    | gate leakage current              | V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C       | -    | -    | 2    | μΑ   |
|                     |                                   | V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C      | -    | -    | 2    | μA   |
|                     |                                   | V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C     | -    | -    | 500  | nA   |
|                     |                                   | $V_{GS} = -4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | -    | -    | 500  | nA   |
| R <sub>DSon</sub>   | drain-source on-state             | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 500 mA; T <sub>j</sub> = 25 °C   | -    | 290  | 380  | mΩ   |
|                     | resistance                        | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 500 mA; T <sub>j</sub> = 150 °C  | -    | 460  | 610  | mΩ   |
|                     |                                   | V <sub>GS</sub> = 2.5 V; I <sub>D</sub> = 400 mA; T <sub>j</sub> = 25 °C   | -    | 420  | 620  | mΩ   |
|                     |                                   | V <sub>GS</sub> = 1.8 V; I <sub>D</sub> = 100 mA; T <sub>j</sub> = 25 °C   | -    | 600  | 1100 | mΩ   |
| g <sub>fs</sub>     | forward transconductance          | $V_{DS}$ = 10 V; $I_{D}$ = 200 mA; $T_{j}$ = 25 °C                         | -    | 1.6  | -    | S    |
| Dynamic ch          | naracteristics                    |  |      |      |      |      |
| Q <sub>G(tot)</sub> | total gate charge                 | $V_{DS}$ = 10 V; $I_{D}$ = 500 mA; $V_{GS}$ = 4.5 V;                       | -    | 0.45 | 0.68 | nC   |
| Q <sub>GS</sub>     | gate-source charge                | T <sub>j</sub> = 25 °C   | -    | 0.15 | -    | nC   |
| $Q_{GD}$            | gate-drain charge                 |  | -    | 0.15 | -    | nC   |
| C <sub>iss</sub>    | input capacitance                 | V <sub>DS</sub> = 10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;                  | -    | 55   | 83   | pF   |
| C <sub>oss</sub>    | output capacitance                | T <sub>j</sub> = 25 °C   | -    | 15   | -    | pF   |
| C <sub>rss</sub>    | reverse transfer capacitance      |  | -    | 7    | -    | pF   |
| t <sub>d(on)</sub>  | turn-on delay time                | $V_{DS}$ = 10 V; $R_L$ = 250 $\Omega$ ; $V_{GS}$ = 4.5 V;                  | -    | 6    | 12   | ns   |
| t <sub>r</sub>      | rise time                         | $R_{G(ext)} = 6 \Omega; T_j = 25 °C$                                       | -    | 4    | -    | ns   |
| $t_{d(off)}$        | turn-off delay time               |  | -    | 86   | 172  | ns   |
| t <sub>f</sub>      | fall time                         |  | -    | 31   | -    | ns   |
| Source-dra          | in diode                          |  | ı    | 1    | -    |      |
| V <sub>SD</sub>     | source-drain voltage              | $I_S = 300 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$    | 0.48 | 0.77 | 1.2  | V    |
|                     |                                   |  |      |      |      |      |

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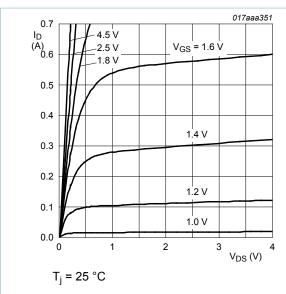
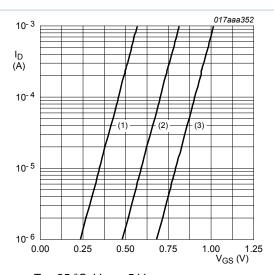


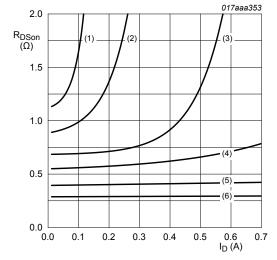
Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_i = 25 \,^{\circ}C; V_{DS} = 5 \,^{\circ}V$ 

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage



 $T_i = 25 \,^{\circ}C$ 

(1)  $V_{GS} = 1.3 \text{ V}$ 

(2)  $V_{GS} = 1.4 \text{ V}$ 

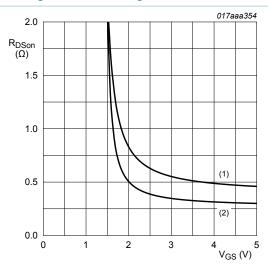
 $(3) V_{GS} = 1.6 V$ 

 $(4) V_{GS} = 1.8 V$ 

 $(5) V_{GS} = 2.5 V$ 

(6)  $V_{GS} = 4.5 \text{ V}$ 

Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



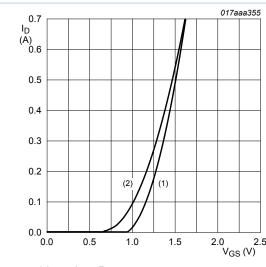
 $I_D = 400 \text{ mA}$ 

(1)  $T_i = 150 \, ^{\circ}C$ 

(2)  $T_i = 25 \, ^{\circ}C$ 

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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 $V_{DS} > I_D \times R_{DSon}$ (1)  $T_i = 25 \, ^{\circ}C$ 

(2)  $T_i = 150 \, ^{\circ}\text{C}$ 

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

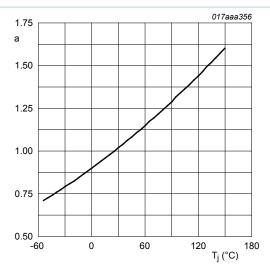
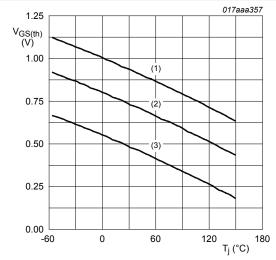


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

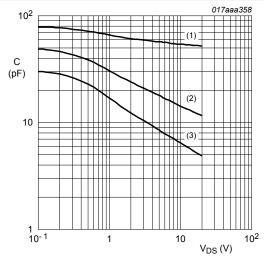
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $I_D$  = 0.25 mA;  $V_{DS}$  =  $V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

- (1) C<sub>iss</sub>
- (2) C<sub>oss</sub>
- (3) C<sub>rss</sub>

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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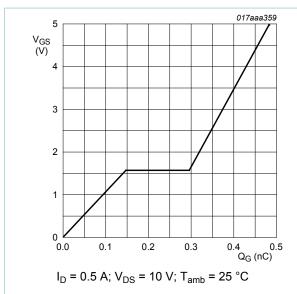


Fig. 14. Gate-source voltage as a function of gate charge; typical values

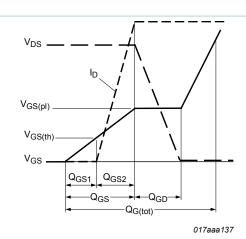
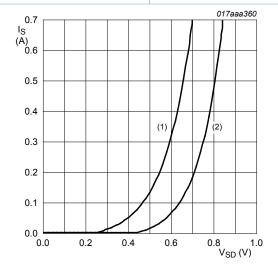


Fig. 15. Gate charge waveform definitions



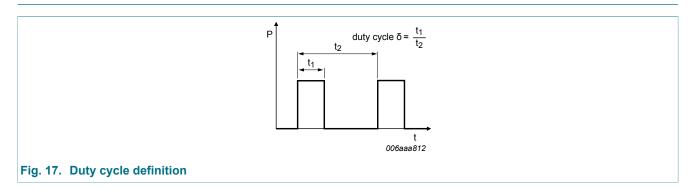
 $V_{GS} = 0 V$ (1)  $T_j = 150 \,^{\circ}C$ 

(2)  $T_i = 25 \, ^{\circ}C$ 

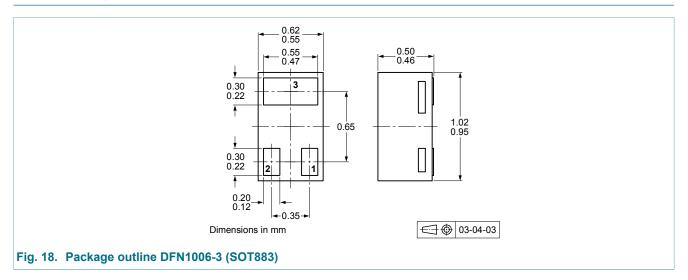
Fig. 16. Source current as a function of source-drain voltage; typical values

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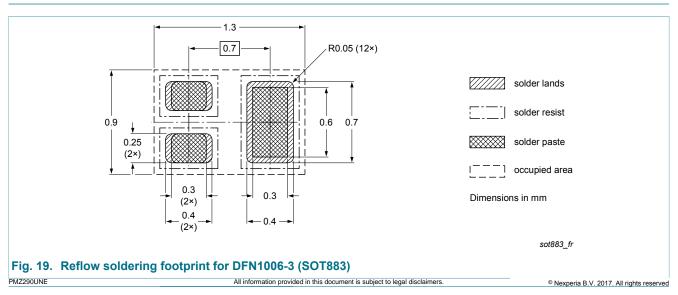
## 11. Test information



# 12. Package outline



# 13. Soldering



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# 14. Revision history

#### Table 8. Revision history

| Data sheet ID | Release date | Data sheet status  | Change notice | Supersedes |
|---------------|--------------|--------------------|---------------|------------|
| PMZ290UNE v.1 | 20140514     | Product data sheet | -             | -          |

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## 15. Legal information

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| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary<br>[short] data<br>sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product<br>[short] data<br>sheet     | Production         | This document contains the product specification.                                     |

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